

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	174	strain\$3 near5 (silicon polysilicon) near10 gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 11:15
L2	257	(relax\$3 strain\$3) near10 (silicon polysilicon) near10 gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 11:15
L3	220	2 and (implant\$3 dop\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 11:15
L4	163	3 and (boron "B")	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 10:55
L5	22	4 and (helium "He" neon "Ne" krypton "Kr" xenon "Xe")	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 11:01
L8	37	strain\$3 near5 (silicon polysilicon) near10 gate	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 11:15
L9	64	(relax\$3 strain\$3) near10 (silicon polysilicon) near10 gate	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 11:16
L10	64	8 9	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 11:16
L11	21	10 and (implant\$3 dop\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 11:16
L12	1008845	(insulat\$3 dielectric)	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 12:02
L13	142936	L12 and (implant\$3 dop\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 12:02
L14	33880	L13 and ((implant\$3 dop\$3) near10 (boron "B"))	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 12:02
L15	680	L14 and ((implant\$3 dop\$3) near10 (helium "He" neon "Ne" krypton "Kr" xenon "Xe"))	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 12:02
L16	542	L15 and (source drain)	US-PGPU B; USPAT; USOCR	OR	ON	2005/04/25 12:02

L17	1105463	(insulat\$3 dielectric)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 12:02
L18	40468	L17 and (implant\$3 dop\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 12:02
L19	11195	L18 and (boron "B" BF3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 12:02
L20	2539	L19 and (helium "He" neon "Ne" krypton "Kr" xenon "Xe")	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 12:02
L22	1160	L20 and (source drain)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/25 12:05